

ON Semiconductor

Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

To learn more about onsemi™, please visit our website at
www.onsemi.com

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NGTD23T120F2

IGBT Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Low $V_{CE(sat)}$ Loss Reduces System Power Dissipation

Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^\circ\text{C}$	V_{CE}	1200	V
DC Collector Current, limited by $T_{J(max)}$	I_C	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, pulse}$	120	A
Gate–Emitter Voltage	V_{GE}	± 20	V
Maximum Junction Temperature	T_J	-55 to $+175$	$^\circ\text{C}$
Short Circuit Withstand Time, $V_{GE} = 15$ V, $V_{CE} = 500$ V, $T_J \leq 150^\circ\text{C}$	T_{SC}	10	μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.
2. T_{pulse} limited by T_{jmax} , 10 μs pulse, $V_{GE} = 15$ V.

MECHANICAL DATA

Parameter	Value	Unit
Die Size	5375 x 4175	μm^2
Emitter Pad Size	See die layout	μm^2
Gate Pad Size	405 x 660	μm^2
Die Thickness	5	mils
Wafer Size	150	mm
Top Metal	5 μm AlSi	
Back Metal	2 μm TiNiAg	
Max possible chips per wafer	546	
Passivation frontside	Oxide–Nitride	
Reject ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28 $^\circ\text{C}$, 30–65%RH	Type: Bare Wafer in Jar Storage time: < 36 months	Type: Die on tape in ring–pack Storage time: < 3 months

ORDERING INFORMATION

Device	Inking?	Shipping
NGTD23T120F2WP	Yes	Bare Wafer in Jar
NGTD23T120F2SWK	Yes	Sawn Wafer on Tape

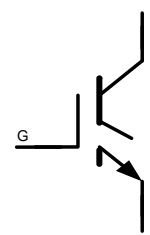


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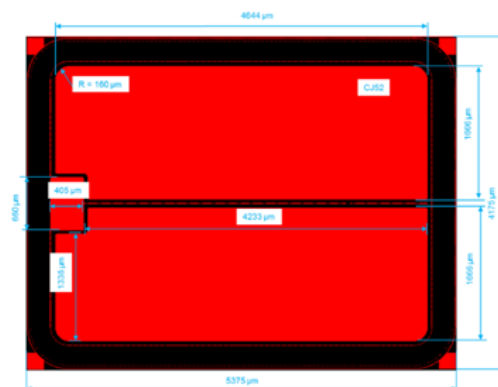
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$V_{RCE} = 1200$ V
 $I_C = \text{Limited by } T_{J(max)}$

IGBT DIE



DIE OUTLINE



NGTD23T120F2

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

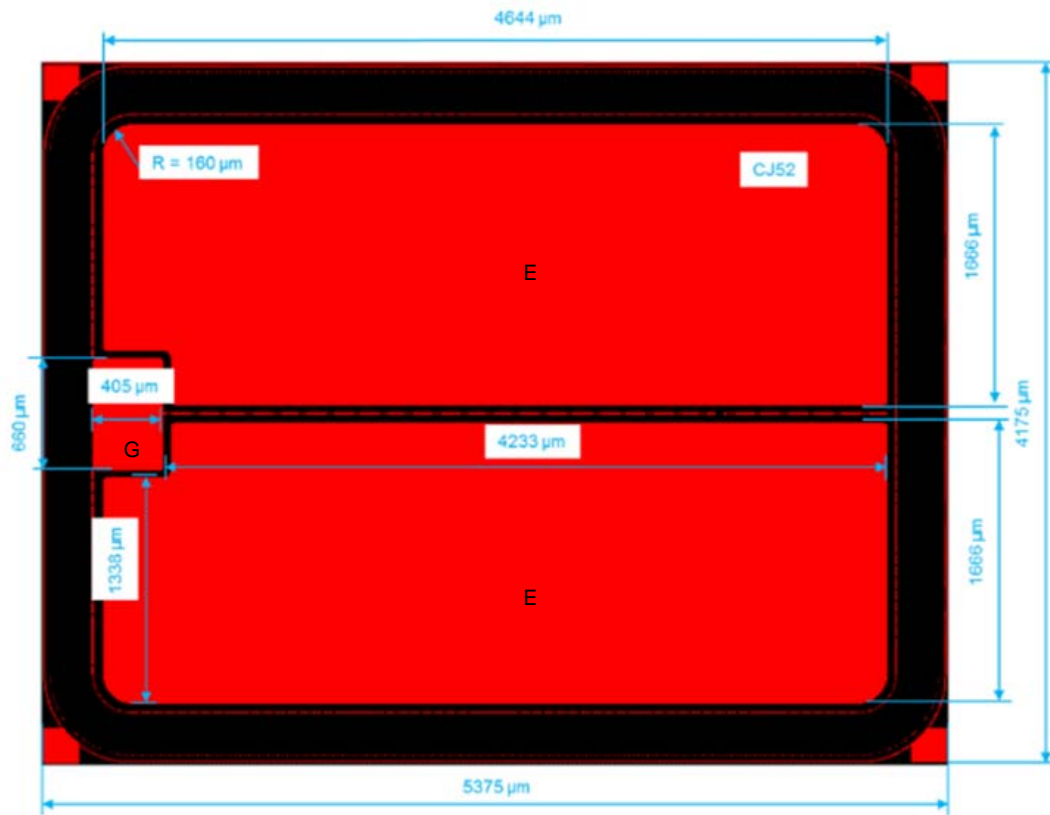
Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
STATIC CHARACTERISTICS						
Collector–Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1200			V
Collector–Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 25\text{ A}$	$V_{CE(sat)}$		1.9	2.2	V
Gate–Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\ \mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector–Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	I_{CES}			1.0	mA
Gate Leakage Current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}			200	nA

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}		5250		pF
Output Capacitance		C_{oes}		170		pF
Reverse Transfer Capacitance		C_{res}		100		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter pad
 G = Gate pad
 All dimensions in μm